SILICON VARACTOR DIODE

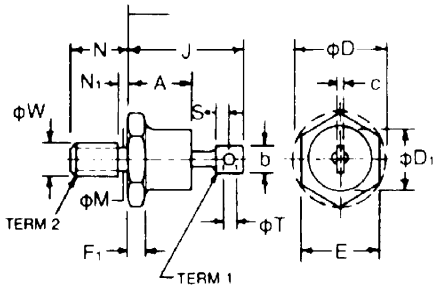
DESCRIPTION:

The **ASI MV1807J1** is a Diffused Epitaxial Varactor Diode Designed for Multiplier Applications.

MAXIMUM RATINGS

I	100 mA
V	80 V
P_{DISS}	21 W @ T_C = 25 °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +175 °C
θ_{JC}	6.0 °C/W

PACKAGE STYLE DO-4



Cathode to case

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A		0.405		10.28
b		0.250		6.35
c				
ΦD		0.505		12.82
ΦD1	0.265	0.424	6.74	10.76
E	0.423	0.438	10.75	11.12
F1	0.075	0.175	1.91	4.44
J	0.600	0.800	15.24	20.32
ΦM	0.163	0.189	4.15	4.80
N	0.422	0.453	10.72	11.50
N1		0.078		1.98
S				
ΦT	0.060	0.095	1.53	2.41
ΦW	10-32	UNF-2A	10-32	UNF-2A

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
V_B	I_R = 10 µA		80			V
C_T	V_R = 6.0 V	f = 1.0 MHz	10.8		13.2	pF
R_S	V_R = 6.0 V	f = 50 MHz		0.25		Ohms
F_{OUT}					1000	MHz
P_{OUT}			25.1			W
F_{IN}					500	MHz
P_{IN}					37.0	W